Truesemi®

September, 2013

SJ-FET

TSK80R240S1/TSA80R240S1
800V N-Channel MOSFET

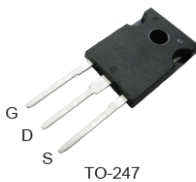
Description

SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.
This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy.
SJ-FET is suitable for various AC/DC power conversion in switching mode operation for higher efficiency.

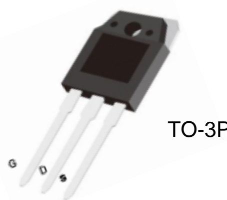
Features

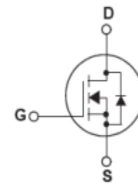
- Multi-Epi process SJ-FET
- 850V @TJ = 150 ℃
- Typ. RDS(on) = 0.22Ω
- Ultra Low Gate Charge (typ. Qg = 27.5nC)
- 100% avalanche tested

TSK80R240S1



TSA80R240S1





Absolute Maximum Ratings

Symbol	Parameter	TSK_A80R240S1	Unit
V_{DSS}	Drain-Source Voltage	800	V
I_D	Drain Current -Continuous (TC = 25℃) -Continuous (TC = 100℃)	18.4* 11.6*	A
I_{DM}	Drain Current – Pulsed (Note 1)	51*	A
V_{GSS}	Gate-Source voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	485	mJ
I_{AR}	Avalanche Current (Note 1)	3.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	1	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	15	V/ns
dVds/dt	Drain Source voltage slope (Vds=640V)	50	V/ns
P_D	Power Dissipation (TC = 25℃)	151	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	℃
T_L	Maximum Lead Temperature for Soldering Purpose,1/8" from Case for 5 Seconds	300	℃

* Drain current limited by maximum junction temperature. Maximum duty cycle D=0.75.

Thermal Characteristics

Symbol	Parameter	TSK_A80R240S1	Unit
$R_{θJC}$	Thermal Resistance, Junction-to-Case	0.83	℃/W
$R_{θCS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	℃/W
$R_{θJA}$	Thermal Resistance, Junction-to-Ambient	62	℃/W

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Electrical Characteristics TC = 25℃ unless otherwise noted

TSK80R240S1/TSA80R240S1 800V N-Channel MOSFET

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA, T_J = 25℃	800	-	-	V
		V_{GS} = 0V, I_D = 250μA, T_J = 150℃	-	850	-	V
ΔBV_{DSS} / Δ_{TJ}	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25℃	-	0.6	-	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 800V, V_{GS} = 0V -T_J = 150℃	-	- 10	1 -	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	-	-	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	-	-	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.5	3.5	4.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 9A	-	0.22	0.26	Ω
g_{FS}	Forward Trans conductance	V_{DS} = 40V, I_D = 18A	-	19	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	-	1290	-	pF
C_{oss}	Output Capacitance		-	380	-	pF
C_{rss}	Reverse Transfer Capacitance		-	22	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400V, I_D = 10A R_G = 25Ω(Note 4)	-	40	-	ns
t_r	Turn-On Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	139	-	ns
t_f	Turn-Off Fall Time		-	21	-	ns
Q_g	Total Gate Charge	V_{DS} = 450V, I_D = 10A V_{GS} = 10V (Note 4)	-	27.5	-	nC
Q_{gs}	Gate-Source Charge		-	6.3	-	nC
Q_{gd}	Gate-Drain Charge		-	11.2	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		-	-	18	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		-	-	51	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_F = 20A	-	1	1.5	V
t_{rr}	Reverse Recovery Time	V_R = 400V, VGS = 0V, I_F = 20A, dI_F/dt =100A/μs	-	710	-	ns
Q_{rr}	Reverse Recovery Charge		-	13	-	μC
I_{rrm}	Peak reverse recovery Current		-	33	-	A

NOTES:
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS}=3.5A, V_{DD}=50V, Starting TJ=25 ℃
3. I_{SD}≤ID, di/dt ≤ 200A/us, V_{DD} ≤ BV_{DSS}, Starting TJ = 25 ℃
4. Essentially Independent of Operating Temperature Typical Characteristics

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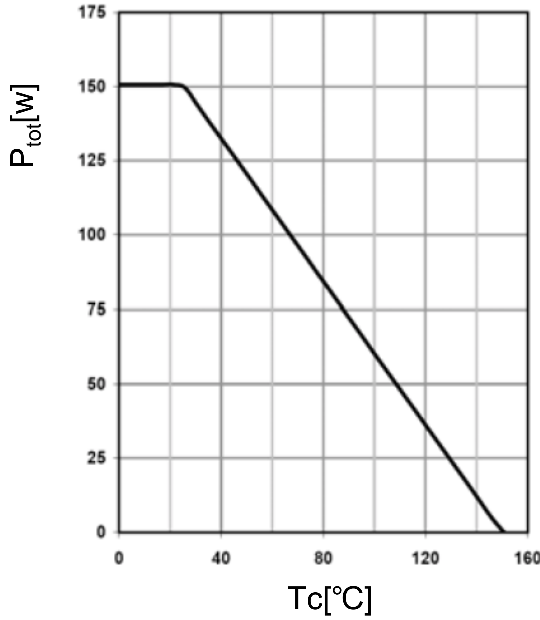
Typical Performance Characteristics

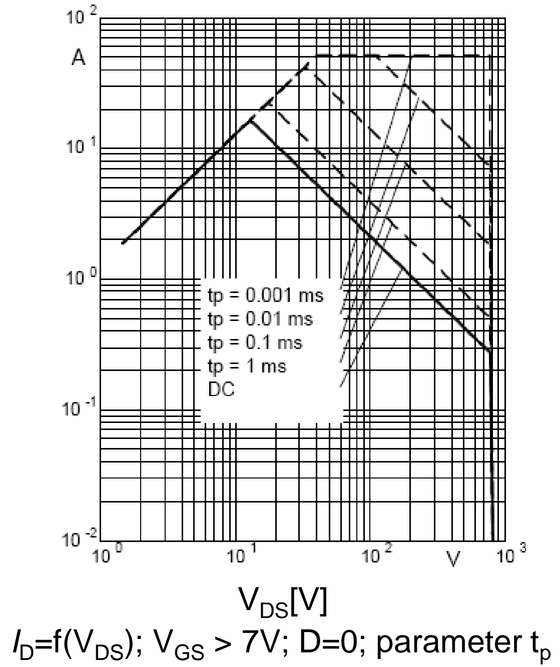
Power dissipation



P_{tot}[W]

Tc[°C]

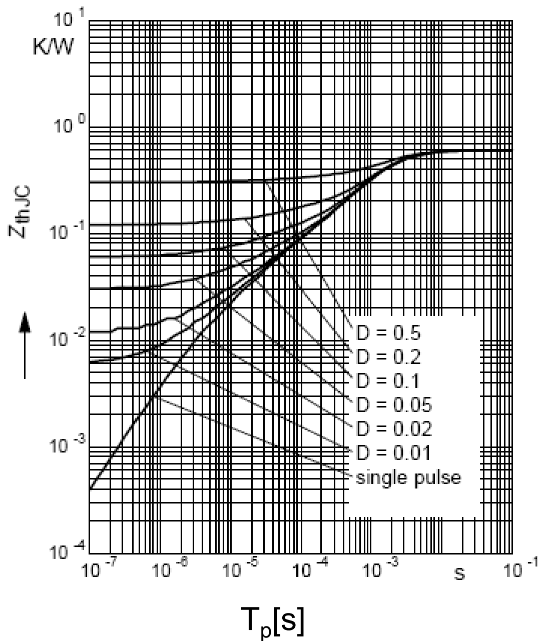
Safe operating area *TC=25*°C



V_{DS}[V]

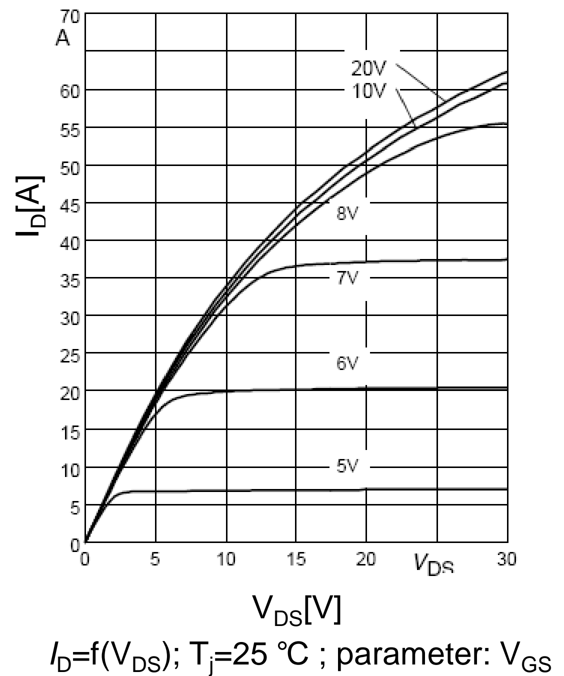
I_D=f(V_{DS}); V_{GS} > 7V; D=0; parameter t_p

Max. transient thermal impedance



T_p[s]

Typ. output characteristics *T_j=25 ℃*



I_D[A]

V_{DS}[V]

I_D=f(V_{DS}); T_j=25 ℃ ; parameter: V_{GS}

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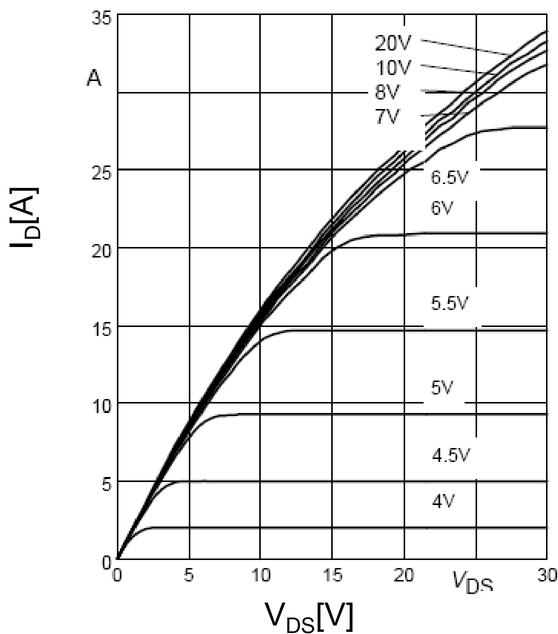
Typical Performance Characteristics

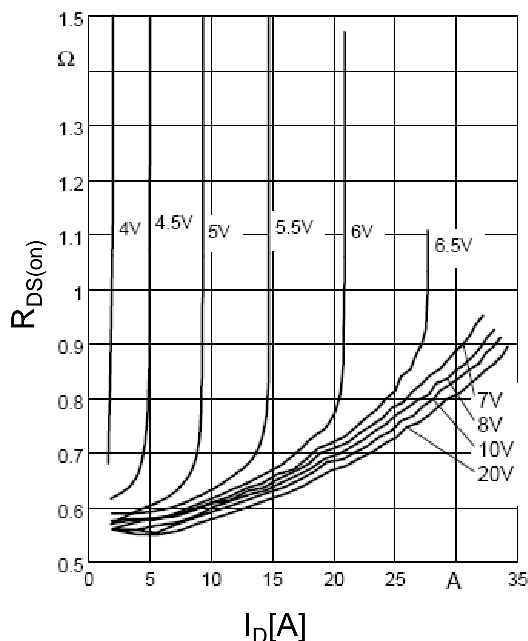
Typ. output characteristics



V_{DS}[V]

I_D=f(V_{DS}); T_j=150 ℃ ; parameter: V_{GS}

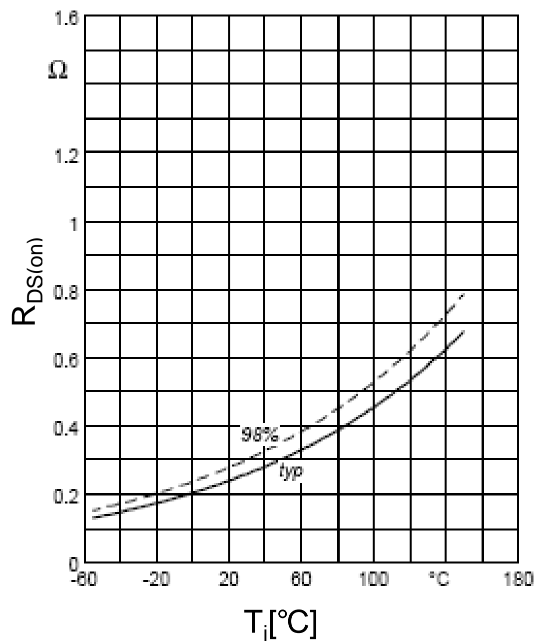
Typ. drain-source on-state resistance



I_D[A]

R_{DS}(on)=f(I_D); T_j=150 ℃ ; parameter:V_{GS}

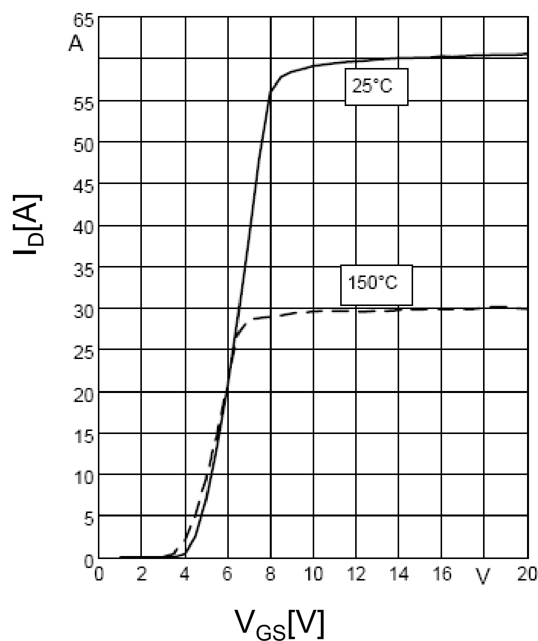
Typ. drain-source on-state resistance



T_j[℃]

R_{DS}(on)=f(T_j); I_D=11 A; V_{GS}=10 V

Typ. transfer characteristics



V_{GS}[V]

I_D=f(V_{GS}); V_{DS}=40V

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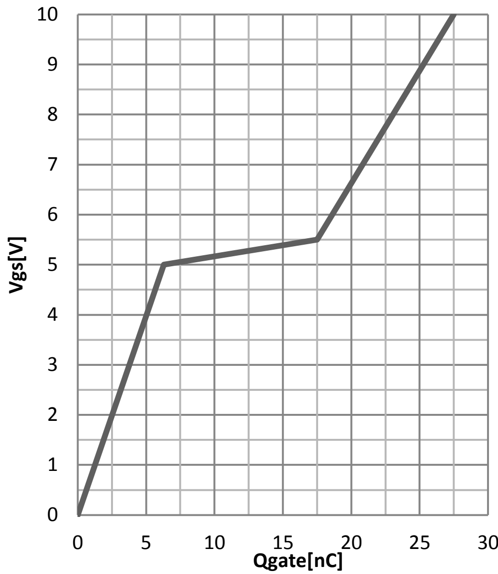
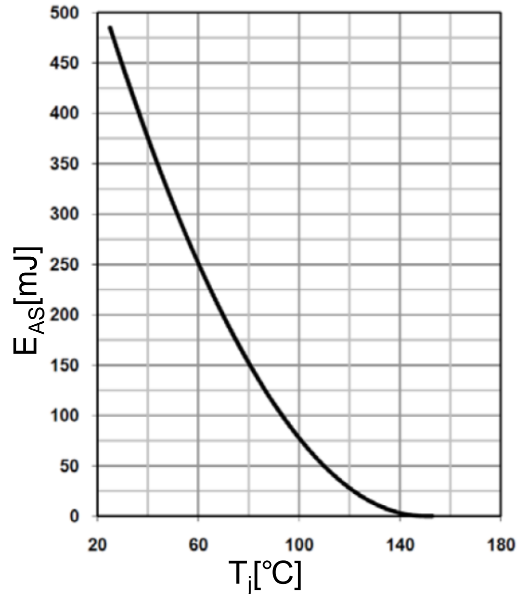
Typical Performance Characteristics

Typ. gate charge



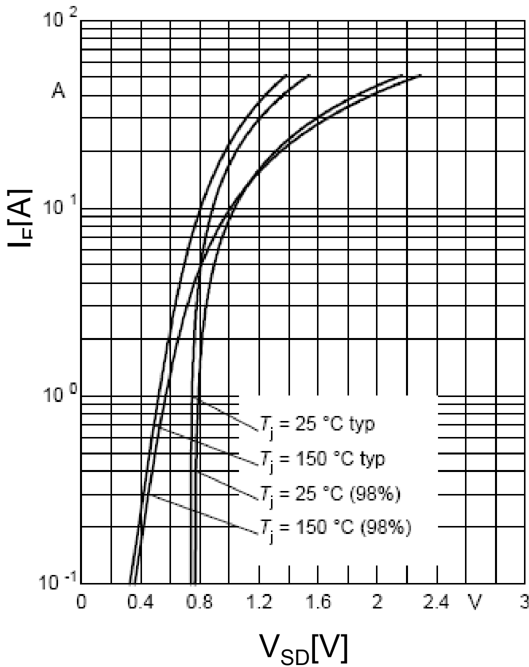
$V_{GS}=f(Q_g)$, $I_D=18$ A pulsed

Avalanche energy



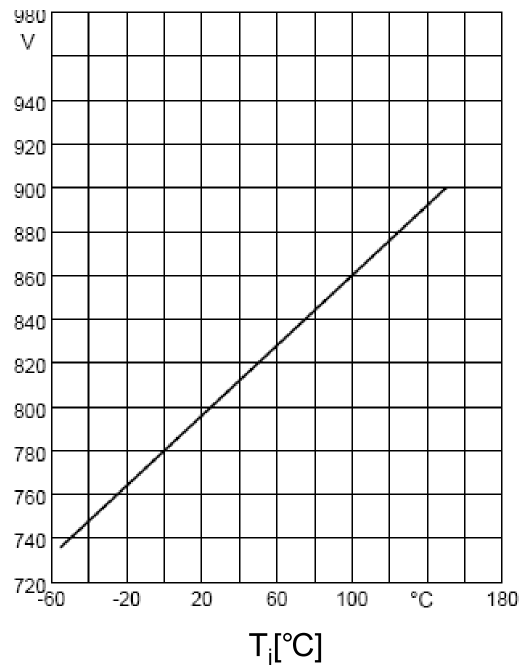
$E_{AS}=f(T_j)$; $I_D=3.5$ A; $V_{DD}=50$ V

Forward characteristics of reverse diode



$I_F=f(V_{SD})$; parameter: T_j

Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$; $I_D=1.0$ mA

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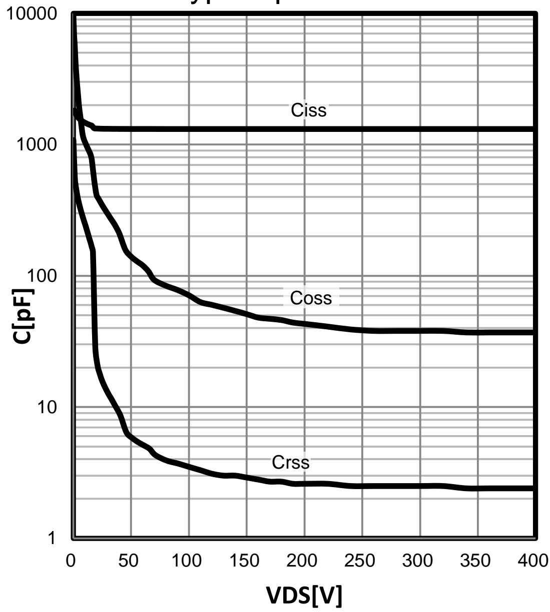
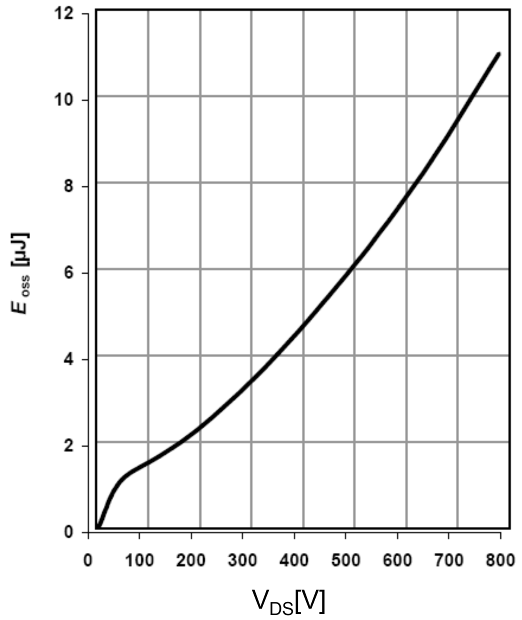


C=f(V_{DS}); V_{GS}=0 V; f=1 MHz



E_{OSS}=f(V_{DS})

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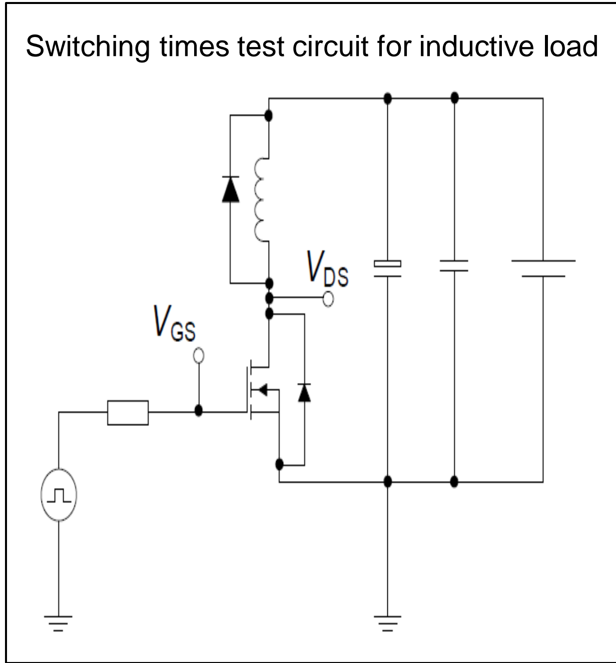
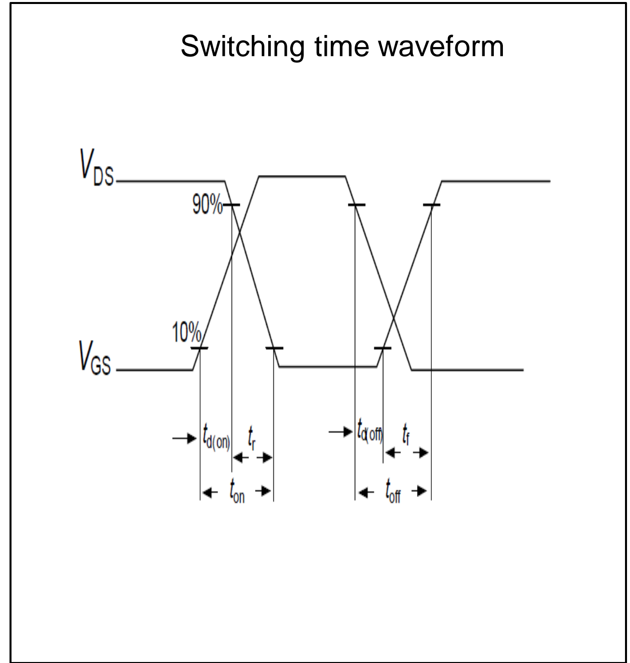
Test circuits

Switching times test circuit and waveform for inductive load

Switching times test circuit for inductive load

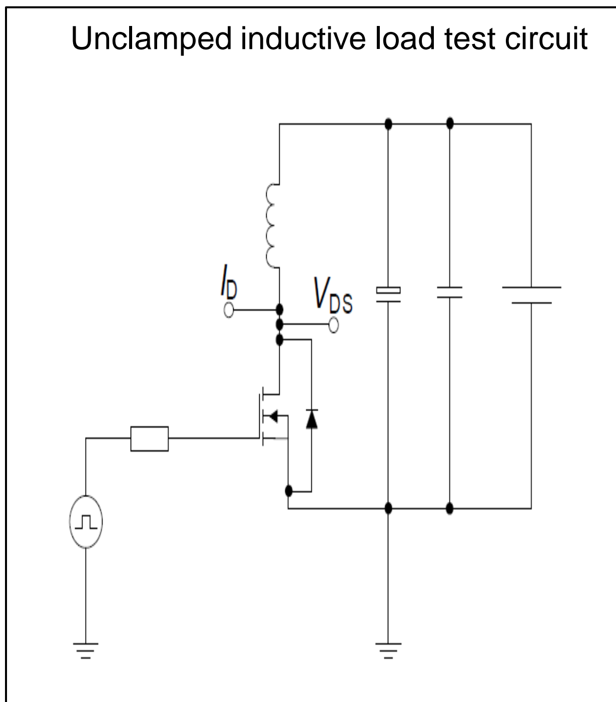


Switching time waveform

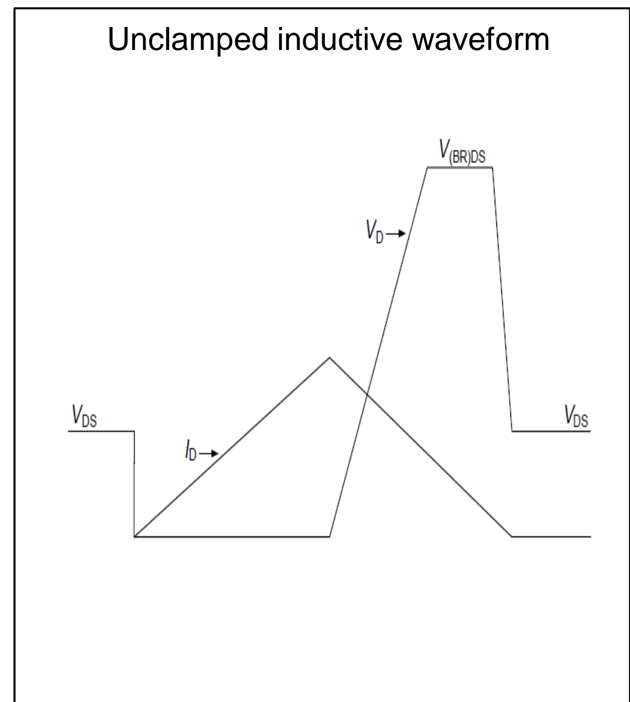


Unclamped inductive load test circuit and waveform

Unclamped inductive load test circuit



Unclamped inductive waveform



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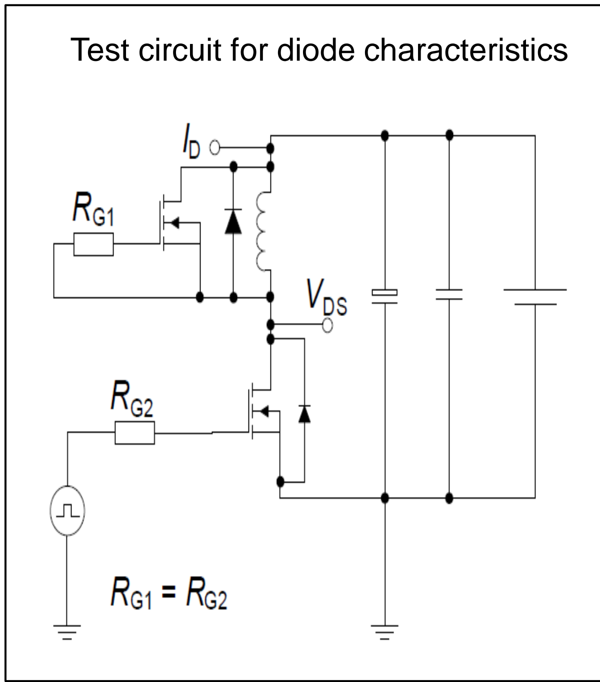
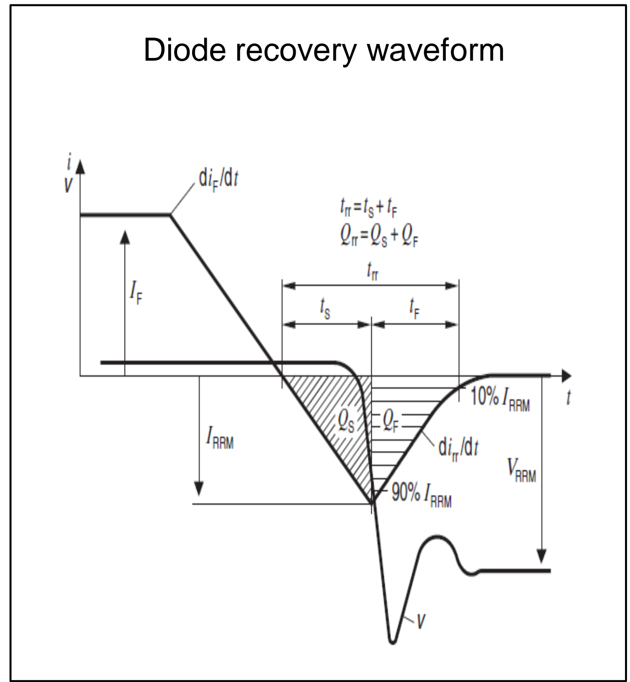
Test circuits

Test circuit and waveform for diode characteristics

Test circuit for diode characteristics



Diode recovery waveform



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